

HiPerFRED²

DPF 240 X 400 NA

tentative

400 V V_{RRM} = $I_{FAV} = 2x \ 120 \ A$ t ... 45 ns =



Backside: isolated

E72873

- Housing: SOT-227B (minibloc)
- Industry standard outline
- · Cu base plate internal DCB isolated

Ratings

- Isolation Voltage 3000 V
- Epoxy meets UL 94V-0
- RoHS compliant

Package:

Symbol Definition Conditions max. Unit min. typ. 400 VRRM max. repetitive reverse voltage $T_{VJ} = 25^{\circ}C$ V $V_{R} = 400 V$ I_R reverse current $T_{VJ} = 25^{\circ}C$ μΑ 5 $V_{R} = 400 V$ $T_{VJ} = 150 \,^{\circ}C$ 1 mΑ VF $I_{F} = 120 A$ $T_{VJ} = 25^{\circ}C$ V forward voltage 1.25 $I_{F} = 240 A$ 1.45 V I_F = 120 A T_{VJ} = 150°C 1.06 V $I_{F} = 240 A$ 1.31 V $T_{c} = 80^{\circ}C$ 120 А I_{fav} d = 0.5 average forward current rectangular V_{F0} T_{VI} = 150°C 0.80 V threshold voltage for power loss calculation only slope resistance 2 mΩ \mathbf{r}_{F} R_{thJC} 0.45 K/W thermal resistance junction to case °C -40 150 T_{VJ} virtual junction temperature w \mathbf{P}_{tot} total power dissipation $T_c = 25^{\circ}C$ 280 $T_{vJ} = 45^{\circ}C$ 2000 А max. forward surge current t = 10 ms (50 Hz), sine IFSM I_{RM} max. reverse recovery current $T_{VJ} = 25^{\circ}C$ 6 А T_{VJ} = 125°C A $I_F = 120 \text{ A}; V_R = 240 \text{ V}$ tbd $-di_{F}/dt = 200 A/\mu s$ $T_{VJ} = 25^{\circ}C$ 45 t_{rr} reverse recovery time ns $T_{vJ} = 125$ °C tbd ns C, $V_{R} = 200 V; f = 1 MHz$ $T_{VJ} = 25^{\circ}C$ junction capacitance 187 pF

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High Performance Fast Recovery Diode Low Loss and Soft Recovery

Parallel legs

Part number

DPF 240 X 400 NA

Features / Advantages:

- Planar passivated chips
- · Very low leakage current
- Very short recovery time Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- · Avalanche voltage rated for reliable operation Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
- Power dissipation within the diode
- Turn-on loss in the commutating switch

Applications:

- · Antiparallel diode for high frequency
- switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode • Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)





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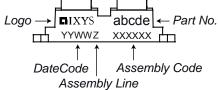
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						Ratings				
Symbol	Definition	Condition	Conditions		min.	typ.	max.	Unit		
I _{RMS}	RMS current	per termina	al				150	Α		
R thCH	thermal resistance case to h	eatsink				0.10		K/W		
T _{stg}	storage temperature				-40		150	°C		
Weight						30		g		
M _D	mounting torque				1.1		1.5	Nm		
Μ _τ	terminal torque				1.1		1.5	Nm		
	isolation voltage	t = 1 second	1		3000			V		
		t = 1 minute			2500			V		
d _{Spp/App}	creepage striking distance	on surface through air	terminal to terminal	10.5	3.2			mm		
d _{Spb/Apb}	creepage striking distance	on surface through air	terminal to backside	8.6	6.8			mm		

Part number

- D = Diode P = HiPerFRED
- F = ultra fast
- 240 = Current Rating [A]
- X = Parallel legs
- 400 = Reverse Voltage [V] NA = SOT-227B (minibloc)

Product Marking



Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DPF 240 X 400 NA	DPF240X400NA	Tube	10	499554

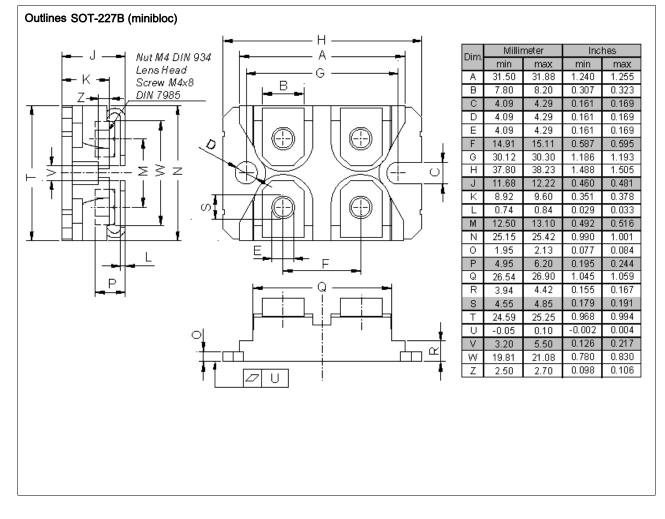
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